

Refine Search

10/6/2,068

Search Results -

Terms	Documents
L5 and fluorocarbon	1

Database:

US Pre-Grant Publication Full-Text Database
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 US OCR Full-Text Database
 EPO Abstracts Database
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 Derwent World Patents Index
 IBM Technical Disclosure Bulletins

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L8

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Search History

DATE: Sunday, March 21, 2004 [Printable Copy](#) [Create Case](#)

<u>Set Name</u> side by side	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u> result set
<i>DB=USPT; PLUR=YES; OP=ADJ</i>			
<u>L8</u>	L5 and fluorocarbon	1	<u>L8</u>
<u>L7</u>	L5 and (deoxidizing or deoxidize or deoxidation)	0	<u>L7</u>
<u>L6</u>	L5 and deoxidizing or deoxidize or deoxidation	2596	<u>L6</u>
<u>L5</u>	L4 and (silicon adj oxide) and (silicon adj nitride) and patterning and trench	10	<u>L5</u>
<u>L4</u>	antireflection and reduction and hydrogen and thermal	269	<u>L4</u>
<u>L3</u>	antireflection and (deoxidize or deoxidizing) and hydrogen and thermal	0	<u>L3</u>
<u>L2</u>	deoxidiz? near7 (antireflection) ¹	0	<u>L2</u>
<u>L1</u>	deoxidizing near4 (antireflection)	0	<u>L1</u>

END OF SEARCH HISTORY

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☐ 1. Document ID: US 6686236 B2

L5: Entry 1 of 10

File: USPT

Feb 3, 2004

US-PAT-NO: 6686236

DOCUMENT-IDENTIFIER: US 6686236 B2

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 2. Document ID: US 6635497 B2

L5: Entry 2 of 10

File: USPT

Oct 21, 2003

US-PAT-NO: 6635497

DOCUMENT-IDENTIFIER: US 6635497 B2

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 3. Document ID: US 6596547 B2

L5: Entry 3 of 10

File: USPT

Jul 22, 2003

US-PAT-NO: 6596547

DOCUMENT-IDENTIFIER: US 6596547 B2

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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☐ 4. Document ID: US 6528386 B1

L5: Entry 4 of 10

File: USPT

Mar 4, 2003

US-PAT-NO: 6528386

DOCUMENT-IDENTIFIER: US 6528386 B1

TITLE: Protection of tungsten alignment mark for FeRAM processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw. De
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☐ 5. Document ID: US 6528328 B1

L5: Entry 5 of 10

File: USPT

Mar 4, 2003

US-PAT-NO: 6528328

DOCUMENT-IDENTIFIER: US 6528328 B1

TITLE: Methods of preventing reduction of irox during PZT formation by metalorganic chemical vapor deposition or other processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw. De
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☐ 6. Document ID: US 6500678 B1

L5: Entry 6 of 10

File: USPT

Dec 31, 2002

US-PAT-NO: 6500678

DOCUMENT-IDENTIFIER: US 6500678 B1

TITLE: Methods of preventing reduction of IrOx during PZT formation by metalorganic chemical vapor deposition or other processing

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw. De
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☐ 7. Document ID: US 6498089 B2

L5: Entry 7 of 10

File: USPT

Dec 24, 2002

US-PAT-NO: 6498089

DOCUMENT-IDENTIFIER: US 6498089 B2

TITLE: Semiconductor integrated circuit device with moisture-proof ring and its manufacture method

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KWC	Draw. De
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☐ 8. Document ID: US 6492222 B1

L5: Entry 8 of 10

File: USPT

Dec 10, 2002

US-PAT-NO: 6492222

DOCUMENT-IDENTIFIER: US 6492222 B1

TITLE: Method of dry etching PZT capacitor stack to form high-density ferroelectric memory devices

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	NUMC	Draw Dc
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☐ 9. Document ID: US 6365512 B1

L5: Entry 9 of 10

File: USPT

Apr 2, 2002

US-PAT-NO: 6365512

DOCUMENT-IDENTIFIER: US 6365512 B1

TITLE: Method and apparatus for a direct buried strap for same level contact interconnections for semiconductor devices

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	NUMC	Draw Dc
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☐ 10. Document ID: US 6303483 B1

L5: Entry 10 of 10

File: USPT

Oct 16, 2001

US-PAT-NO: 6303483

DOCUMENT-IDENTIFIER: US 6303483 B1

TITLE: Method of manufacturing semiconductor device

Full	Title	Citation	Front	Review	Classification	Date	Reference	Claims	NUMC	Draw Dc
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Terms	Documents
L4 and (silicon adj oxide) and (silicon adj nitride) and patterning and trench	10

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☐ 1. Document ID: US 6492222 B1

L8: Entry 1 of 1

File: USPT

Dec 10, 2002

US-PAT-NO: 6492222

DOCUMENT-IDENTIFIER: US 6492222 B1

TITLE: Method of dry etching PZT capacitor stack to form high-density ferroelectric memory devices

Full	Title	Citation	Front	Review	Classification	Date	Reference			Claims	KMC	Draw D
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Terms	Documents
L5 and fluorocarbon	1

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